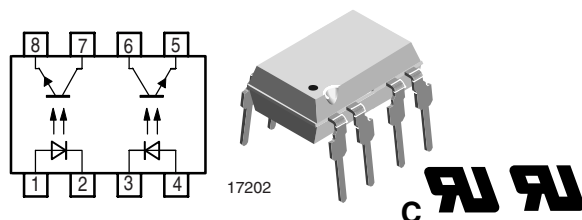


## Optocoupler, Phototransistor Output, Dual Channel



### DESCRIPTION

The MCT6H and MCT62H consist of a phototransistor optically coupled to a gallium arsenide infrared emitting diode in a 6-lead plastic dual inline package.

The elements are mounted on one leadframe, providing a fixed distance between input and output for highest safety requirements.

### FEATURES

- Current transfer ratio (CTR) of typical 100 %
- Isolation test voltage  $V_{ISO} = 5300 V_{RMS}$
- Low temperature coefficient of CTR
- Low coupling capacitance of typical 0.3 pF
- Wide ambient temperature range
- Lead (Pb)-free component
- Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC



**RoHS**  
COMPLIANT

### APPLICATIONS

- Galvanically separated circuits
- Non-interacting switches

### AGENCY APPROVALS

- UL1577, file no. E76222 system code U, double protection

### ORDER INFORMATION

| PART   | REMARKS            |
|--------|--------------------|
| MCT6H  | CTR > 50 %, DIP-8  |
| MCT62H | CTR > 100 %, DIP-8 |

#### Note

MCT6H and MCT62H are marked as MCT6 and MCT62 respectively.

### ABSOLUTE MAXIMUM RATINGS <sup>(1)</sup>

| PARAMETER                            | TEST CONDITION                | PART | SYMBOL     | VALUE         | UNIT      |
|--------------------------------------|-------------------------------|------|------------|---------------|-----------|
| <b>INPUT</b>                         |                               |      |            |               |           |
| Reverse voltage                      |                               |      | $V_R$      | 6             | V         |
| Forward current                      |                               |      | $I_F$      | 60            | mA        |
| Forward surge current                | $t_p \leq 10 \mu s$           |      | $I_{FSM}$  | 1.5           | A         |
| Power dissipation                    |                               |      | $P_{diss}$ | 100           | mW        |
| Junction temperature                 |                               |      | $T_j$      | 125           | °C        |
| <b>OUTPUT</b>                        |                               |      |            |               |           |
| Collector emitter voltage            |                               |      | $V_{CEO}$  | 70            | V         |
| Emitter collector voltage            |                               |      | $V_{ECO}$  | 7             | V         |
| Collector current                    |                               |      | $I_C$      | 50            | mA        |
| Collector peak current               | $t_p/T = 0.5, t_p \leq 10 ms$ |      | $I_{CM}$   | 100           | mA        |
| Power dissipation                    |                               |      | $P_{diss}$ | 150           | mW        |
| Junction temperature                 |                               |      | $T_j$      | 125           | °C        |
| <b>COUPLER</b>                       |                               |      |            |               |           |
| AC isolation test voltage (RMS)      | $t = 1.0 min$                 |      | $V_{ISO}$  | 5000          | $V_{RMS}$ |
| Total power dissipation              |                               |      | $P_{tot}$  | 250           | mW        |
| Ambient temperature range            |                               |      | $T_{amb}$  | - 55 to + 100 | °C        |
| Storage temperature range            |                               |      | $T_{stg}$  | - 55 to + 125 | °C        |
| Soldering temperature <sup>(2)</sup> | 2 mm from case, $t \leq 10 s$ |      | $T_{sld}$  | 260           | °C        |

#### Notes

<sup>(1)</sup>  $T_{amb} = 25 \text{ °C}$ , unless otherwise specified.

Stresses in excess of the absolute maximum ratings can cause permanent damage to the device. Functional operation of the device is not implied at these or any other conditions in excess of those given in the operational sections of this document. Exposure to absolute maximum ratings for extended periods of the time can adversely affect reliability.

<sup>(2)</sup> Refer to wave profile for soldering conditions for through hole devices.



| <b>ELECTRICAL CHARACTERISTICS <sup>(1)</sup></b> |                                                                                |             |      |           |      |           |
|--------------------------------------------------|--------------------------------------------------------------------------------|-------------|------|-----------|------|-----------|
| PARAMETER                                        | TEST CONDITION                                                                 | SYMBOL      | MIN. | TYP.      | MAX. | UNIT      |
| <b>INPUT</b>                                     |                                                                                |             |      |           |      |           |
| Forward voltage                                  | $I_F = 50 \text{ mA}$                                                          | $V_F$       |      | 1.25      | 1.6  | V         |
| <b>OUTPUT</b>                                    |                                                                                |             |      |           |      |           |
| Collector emitter voltage                        | $I_C = 1 \text{ mA}$                                                           | $V_{CEO}$   | 70   |           |      | V         |
| Emitter collector voltage                        | $I_E = 100 \text{ }\mu\text{A}$                                                | $V_{ECO}$   | 7    |           |      | V         |
| Collector dark current                           | $V_{CE} = 20 \text{ V}$ , $I_F = 0$ , $E = 0$                                  | $I_{CEO}$   |      |           | 100  | nA        |
| <b>COUPLER</b>                                   |                                                                                |             |      |           |      |           |
| DC isolation test voltage                        | $t = 2 \text{ s}$                                                              | $V_{ISO}$   | 5000 |           |      | $V_{RMS}$ |
| Isolation resistance                             | $V_{IO} = 1000 \text{ V}$ ,<br>40 % relative humidity                          | $R_{IO}$    |      | $10^{12}$ |      | $\Omega$  |
| Collector emitter saturation voltage             | $I_F = 10 \text{ mA}$ , $I_C = 1 \text{ mA}$                                   | $V_{CEsat}$ |      |           | 0.3  | V         |
| Cut off frequency                                | $I_F = 10 \text{ mA}$ , $V_{CE} = 5 \text{ V}$ ,<br>$R_L = 100 \text{ }\Omega$ | $f_C$       |      | 100       |      | kHz       |
| Coupling capacitance                             | $f = 1 \text{ MHz}$                                                            | $C_k$       |      | 0.3       |      | pF        |

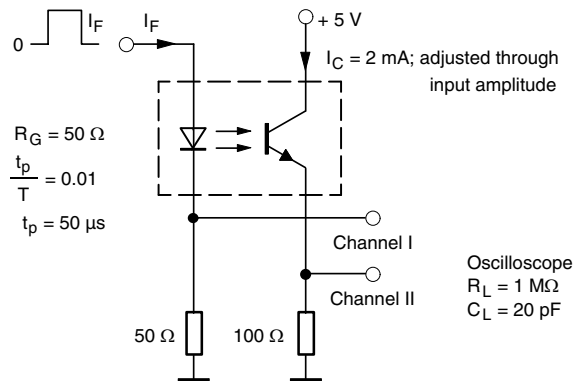
**Note**

<sup>(1)</sup>  $T_{amb} = 25 \text{ }^\circ\text{C}$ , unless otherwise specified.

Minimum and maximum values are testing requirements. Typical values are characteristics of the device and are the result of engineering evaluation. Typical values are for information only and are not part of the testing requirements.

| <b>CURRENT TRANSFER RATIO</b> |                                                |        |        |      |      |      |      |
|-------------------------------|------------------------------------------------|--------|--------|------|------|------|------|
| PARAMETER                     | TEST CONDITION                                 | PART   | SYMBOL | MIN. | TYP. | MAX. | UNIT |
| $I_C/I_F$                     | $V_{CE} = 5 \text{ V}$ , $I_F = 5 \text{ mA}$  | MCT6H  | CTR    | 50   | 100  |      | %    |
|                               | $V_{CE} = 5 \text{ V}$ , $I_F = 10 \text{ mA}$ | MCT6H  | CTR    | 60   | 120  |      | %    |
|                               | $V_{CE} = 5 \text{ V}$ , $I_F = 5 \text{ mA}$  | MCT62H | CTR    | 100  | 200  |      | %    |

| <b>SWITCHING CHARACTERISTICS</b> |                                                                                           |           |      |      |      |               |
|----------------------------------|-------------------------------------------------------------------------------------------|-----------|------|------|------|---------------|
| PARAMETER                        | TEST CONDITION                                                                            | SYMBOL    | MIN. | TYP. | MAX. | UNIT          |
| Delay time                       | $V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \text{ }\Omega$<br>(see figure 1) | $t_d$     |      | 3    |      | $\mu\text{s}$ |
| Rise time                        | $V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \text{ }\Omega$<br>(see figure 1) | $t_r$     |      | 3    |      | $\mu\text{s}$ |
| Fall time                        | $V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \text{ }\Omega$<br>(see figure 1) | $t_f$     |      | 4.7  |      | $\mu\text{s}$ |
| Storage time                     | $V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \text{ }\Omega$<br>(see figure 1) | $t_s$     |      | 0.3  |      | $\mu\text{s}$ |
| Turn-on time                     | $V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \text{ }\Omega$<br>(see figure 1) | $t_{on}$  |      | 6    |      | $\mu\text{s}$ |
| Turn-off time                    | $V_S = 5 \text{ V}$ , $I_C = 2 \text{ mA}$ , $R_L = 100 \text{ }\Omega$<br>(see figure 1) | $t_{off}$ |      | 5    |      | $\mu\text{s}$ |



95 10804

Fig. 1 - Test Circuit, non Saturated Operation

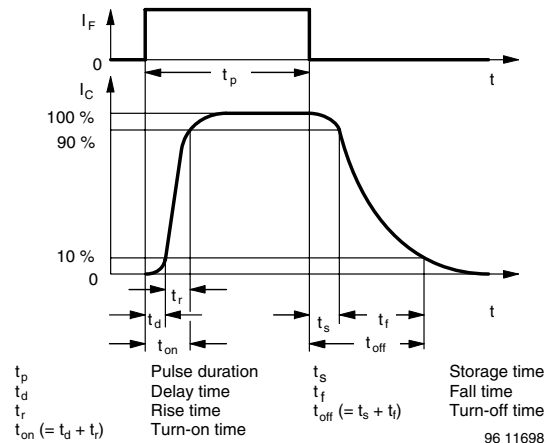


Fig. 2 - Switching Times

## TYPICAL CHARACTERISTICS

$T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified

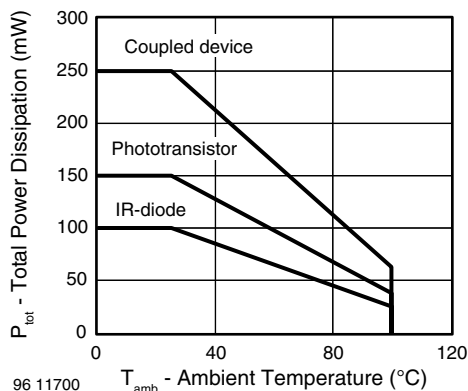


Fig. 3 - Total Power Dissipation vs. Ambient Temperature

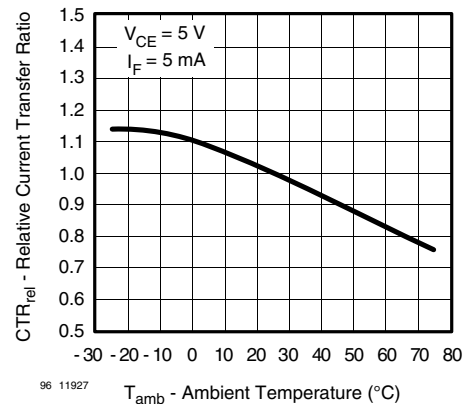


Fig. 5 - Relative Current Transfer Ratio vs. Ambient Temperature

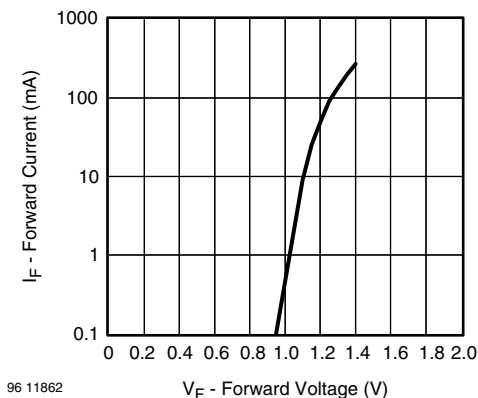


Fig. 4 - Forward Current vs. Forward Voltage

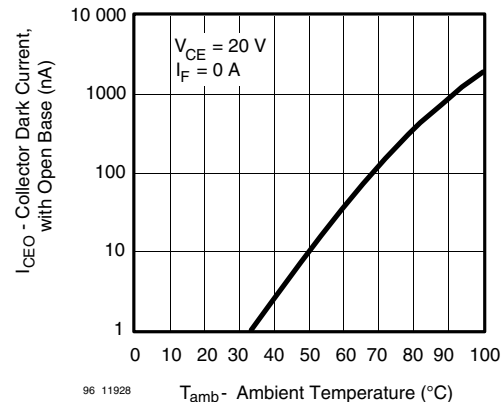


Fig. 6 - Collector Dark Current vs. Ambient Temperature

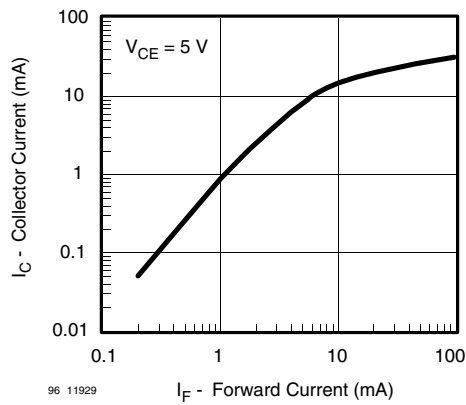


Fig. 7 - Collector Current vs. Forward Current

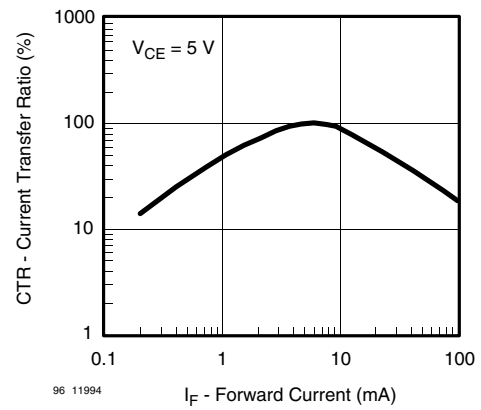


Fig. 10 - Current Transfer Ratio vs. Forward Current

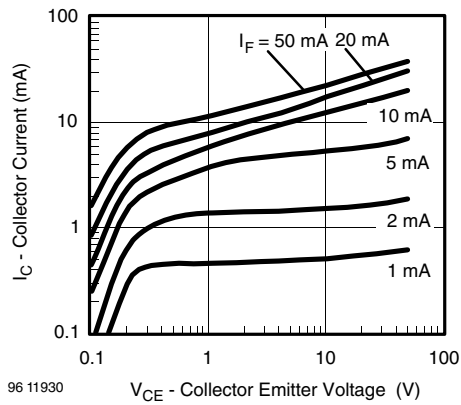


Fig. 8 - Collector Current vs. Collector Emitter Voltage

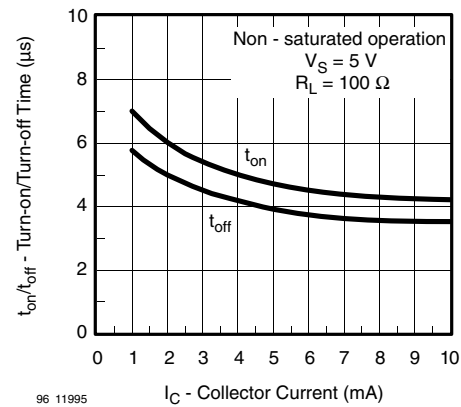


Fig. 11 - Turn-on/Turn-off Time vs. Collector Current

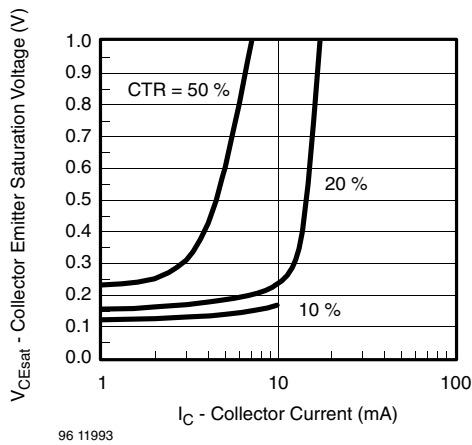


Fig. 9 - Collector Emitter Saturation Voltage vs. Collector Current

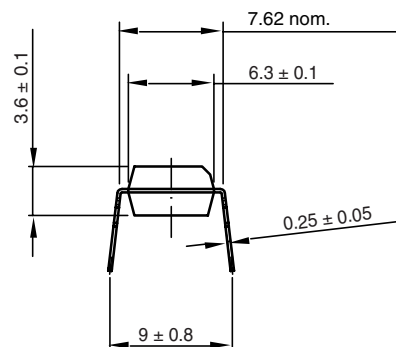
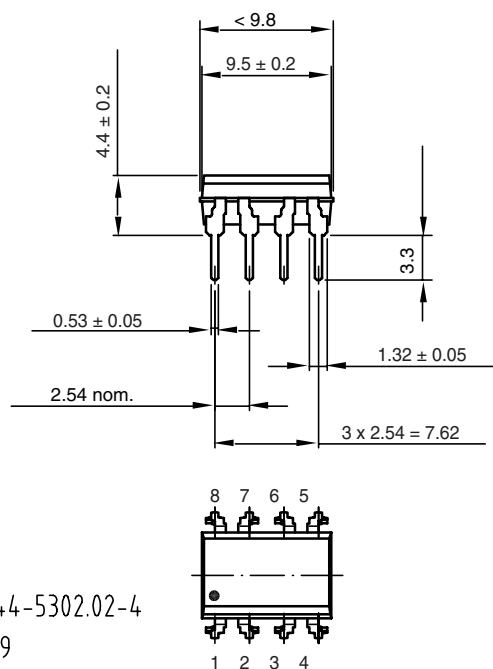
# MCT6H, MCT62H

Vishay Semiconductors

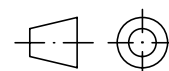
Optocoupler, Phototransistor  
Output, Dual Channel



## PACKAGE DIMENSIONS in inches (millimeters)



Weight: ca. 0.55 g  
Creepage distance:  $> 6 \text{ mm}$   
Air path:  $> 6 \text{ mm}$   
after mounting on PC board



technical drawings  
according to DIN  
specifications

Drawing-No.: 6.544-5302.02-4  
Issue: 4; 02.06.99

14784

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1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

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2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA.
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

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